

Tunneling of magnetization versus spin–phonon and spin–spin transitions in $\text{LiY}_{0.998}\text{Ho}_{0.002}\text{F}_4$

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Abstract

Strong hyperfine coupling in a 0.2% Holmium doped LiYF_4 single crystal induces staircaselike hysteresis loops of the magnetization at very low temperatures. The field sweep rate dependence of hysteresis loops allows the study of two different regimes in the magnetic relaxation of these weakly coupled magnetic moments. At slow field sweep rates, quantum tunneling of the magnetization occurs at avoided level crossings in the low-energy scheme of a single ion Ho^{3+} . At faster sweep rates, nonequilibrated spin–phonon and spin–spin transitions, mediated by weak dipolar interactions, lead to magnetization oscillations and additional steps.

Keywords: Magnetization-quantum tunneling; Hyperfine interactions; Phonons-bottleneck; Rare earth-ions; Spin-phonon interactions

Low frequencies quantum fluctuations of large magnetic moments, with a large uniaxial anisotropy, are reminiscent of mesoscopic magnetism. At very low temperature, the slow quantum dynamics associated with small tunneling gaps leads to staircaselike hysteresis loops. Discovered before in molecular magnets (see [1] for a review), the quantum tunneling of the magnetization was recently observed in a weakly doped holmium fluoride, namely $\text{LiY}_{0.998}\text{Ho}_{0.002}\text{F}_4$, at slow field sweep rates and very low temperatures [2]. As a result of a weak coupling to the cryostat at subkelvin temperatures, the sample is strongly sensitive to internal heating, due to phonon emission during the magnetization reversal. An increase of the field sweep rate thus leads to a crossover from a quantum behavior at low rates to a magnetic relaxation regime dominated by spin–spin and spin–phonon interactions in a phonon bottleneck regime. In this paper, we present field sweep rate dependent hysteresis loops, at a cryostat temperature $T = 40$ mK, which evidence this crossover. The weak dependence of hysteresis loops to a transverse applied field at fast sweep rates, compared to the strong dependence observed in the tunneling regime, also highlights this change in the nature of the dominant relaxation mechanism.

Diluted rare-earth ions in a nonmagnetic insulating single crystal are mainly investigated for applications in high-power laser diodes [3]. In magnetism, very diluted samples are also relevant to study a nearly single ion quantum behavior of weakly coupled magnetic moments. The studied crystal has a tetragonal scheelite structure with S_4 point symmetry group at Ho^{3+} sites. Due to the crystal field, each magnetic ion of ^{165}Ho is characterized by an Ising-type ground state doublet. At very low temperatures, the system should be equivalent to a two-level system, with the magnetization lying along the c -axis. However, the electronic magnetic moment is strongly coupled to its nuclear spin ($I = 7/2$) which split each ground state into eight levels, leading to level crossings in the Zeeman diagram for resonant values $\mu_0 H_n = n \times 23$ mT ($-7 \leq n \leq 7$), as already discussed in [2]. The low excited states in this diagram are shown in Fig. 1a). Because of a crystal field induced hyperfine level repulsion, there are some strongly avoided level crossings. Note that the degeneracies of the other level crossings are also removed by internal fields fluctuations. Magnetic measurements were

made at $0.04 < T < 1$ K and for $\mu_0 H < 2$ T, with a micro-SQUID magnetometer [4] allowing field sweep rates up to 1 T/s. The crystal is first saturated in a large positive field applied along the c -axis $\mu_0 H_{\text{sat}} \approx 0.3$ T, and then the field H_z is swept between $\pm H_{\text{sat}}$. At slow field sweep rates and very low temperatures, quantum tunneling at avoided level crossings leads to staircaselike hysteresis loops, as shown in Fig. 1b). The well-defined steps, observed at $T = 40$ mK for a field sweep rate $v = 0.11$ mT/s, agree with the energy level scheme shown above. This quantum relaxation is strongly enhanced by a constant transverse field, as a result of a rapid increase of the tunnel splittings [2]. Furthermore, hysteresis loops are also very sensitive to the field sweep rate, as shown in Fig. 2a). With the increase of the sweep rate, magnetization steps happen before field inversion and hysteresis develop in larger applied fields, showing the influence of the phonon bath. In addition, the observed hysteresis loops depend on sample thermalization, showing the spin-phonon system is not at equilibrium with the cryostat (phonon bottleneck) [5–7]. When the field is swept back and forth after cooling the sample under H_{sat} , a stationary regime occurs with reduced hysteresis compared to the first magnetization curve (Fig. 2b). Such a behavior occurs because of phonon emission during the magnetization reversal. The phonon bottleneck induces an increase of the internal temperature in the sample, which depends on the sweep rate. A hysteresis loop measured at $T = 50$ mK for a much faster field sweep rate ($v = 0.3$ T/s) is shown in Fig. 3a). A succession of equally spaced large and weak magnetization steps occur at fields H_n , with $-14 \leq 2n \leq 14$. The larger ones, with integer n , are associated with several equally spaced level crossings and the smaller steps, with half integer n , fall just in between when the levels are equally spaced. Equilibrium within the spin system is due to either quantum fluctuations at avoided level crossings (integer n) or to spin-phonon transitions and/or cross-spin relaxation, allowed by weak dipolar interactions, when energy levels are almost equally spaced (integer and half integer n) [7,8]. Spin-spin interactions allow two additional steps for $n = 8$ and $n = 9$, at fields with equally spaced levels but no level crossing (inset of Fig. 3b). If the field sweep is suddenly stopped, the spin-phonon system exchanges energy with the cryostat and the magnetization relaxes toward the equilibrium

curve. A small transverse applied field only increases the zero-field magnetization step (Fig. 4), showing enhanced quantum fluctuations. Other resonances and small magnetization steps, dominated by cross-spin relaxation, are not affected by a small transverse field, if small enough ($\mu_0 H_T \lesssim 20$ mT). This is emphasized in Fig. 4 where the small step at $\mu_0 H_{1/2} = 11.5$ mT remains the same when increasing H_T , as do all the magnetization steps before field inversion if the transverse field is not too large. As expected for the magnetization step at $\mu_0 H_1 = 23$ mT, which involves a large tunneling gap, the increase of this step requires larger transverse fields, as high as 200 mT.

In conclusion, the field sweep rate dependence of hysteresis loops at very low temperatures clearly evidences a crossover between two different regime in the magnetic relaxation of weakly coupled magnetic moments in $\text{LiY}_{0.998}\text{Ho}_{0.002}\text{F}_4$. At slow sweep rates, quantum tunnelling of the magnetization occurs and is monitored by both crystal field and hyperfine couplings. At faster field sweep rates, additional magnetization steps are attributed to spin-phonon transitions and cross-spin relaxation in a phonon bottleneck regime.

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LIST OF FIGURES CAPTIONS

FIG. 1 Up a): Zeeman diagram of the split electronic ground state doublet by the hyperfine interaction (low-energy part). The level crossings occur for resonant values of the longitudinal field H_n . Down b): Hysteresis loops at $T \approx 40$ mK and for $v = 0.11$ mT/s showing quantum tunneling of the magnetization.

FIG. 2 Up a): Hysteresis loops for faster sweep rates at $T \approx 40$ mK, $v = 0.27$ mT/s (full line) and $v = 8.7$ mT/s (dotted line). Down b): Hysteresis loops at $T \approx 40$ mK and for $v = 28.7$ mT/s. As shown by the dashed line, a larger hysteresis occurs for the first magnetization reversal (smaller internal temperature).

FIG. 3 Up a): Hysteresis loops at $T = 50$ mK and for $v = 0.3$ T/s. Several magnetization steps are observed for resonant values of the applied field $\mu_0 H_n \approx n \times 23$ mT (see inset, H_n values are deduced from Fig. 3b). Down b): Derivative of the loop shown in a) for a decreasing field. The two additional measured steps shown in the inset, for $n = 8$ and $n = 9$, are associated with cross-spin relaxation only.

FIG. 4 Part of the hysteresis loops at $T = 50$ mK, for $v = 0.3$ T/s and for several transverse applied fields ($dH_z/dt \neq 0$). The shifted magnetization curves $m - \Delta m_{1/2}$, with $m = M/M_s$ and $\Delta m_{1/2} = m(H_{1/2}, H_T) - m(H_{1/2}, 0)$, are used to highlight the small magnetization step at $\mu_0 H_{1/2} = 11.5$ mT.

FIGURES

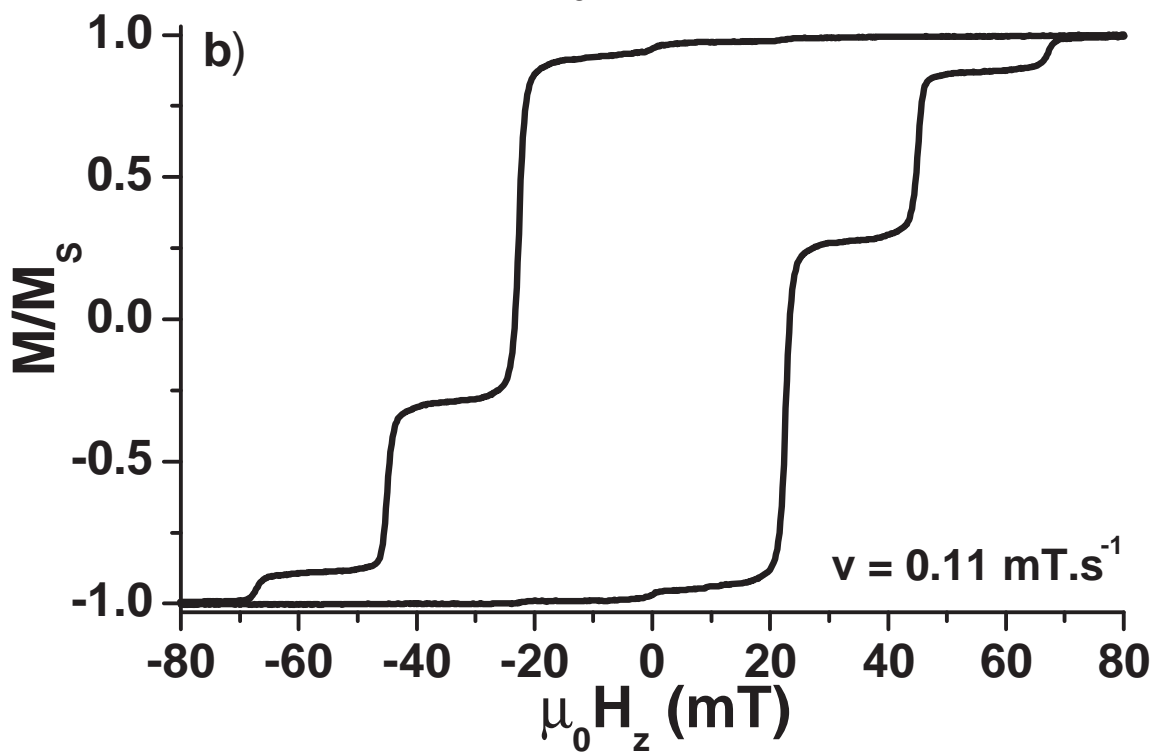
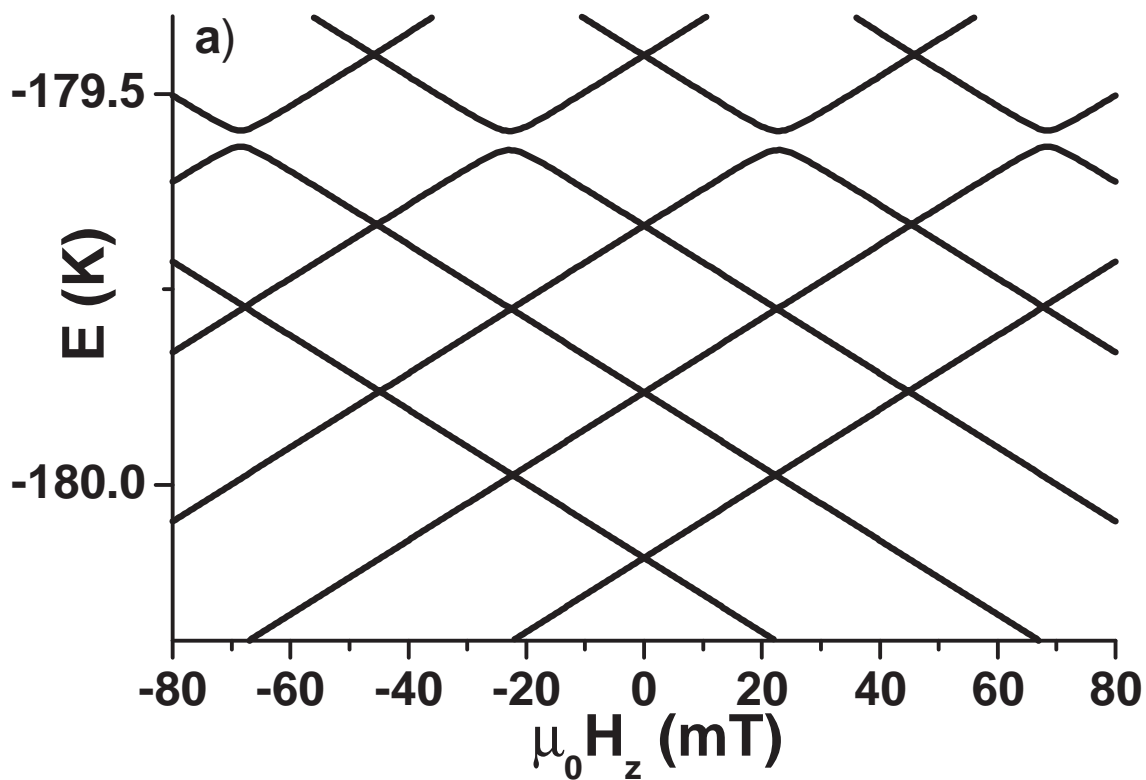


FIG. 1. R. Giraud

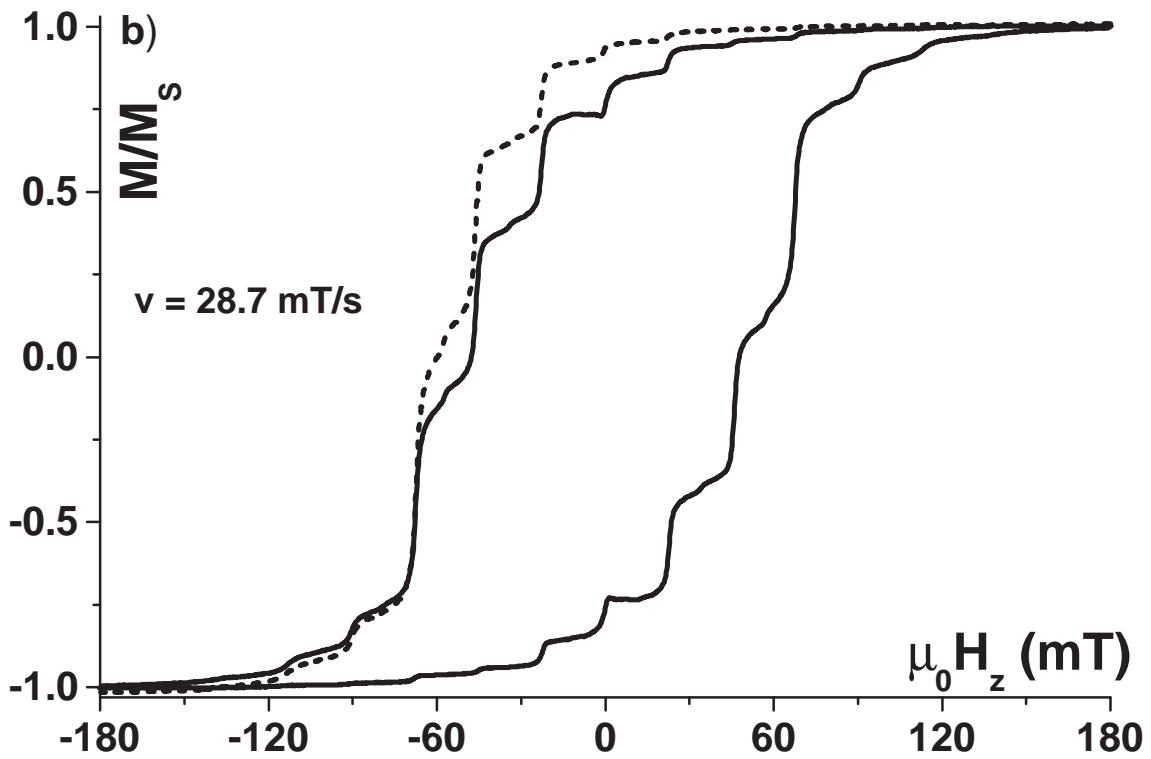
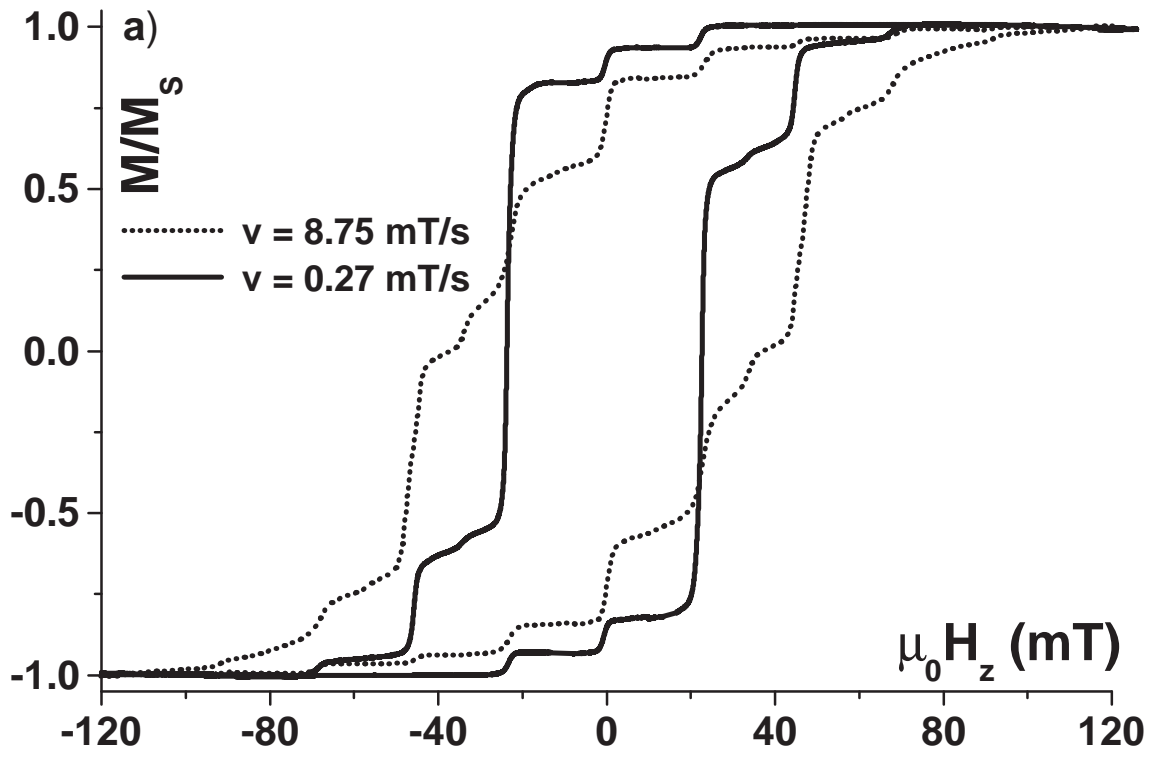


FIG. 2. R. Giraud

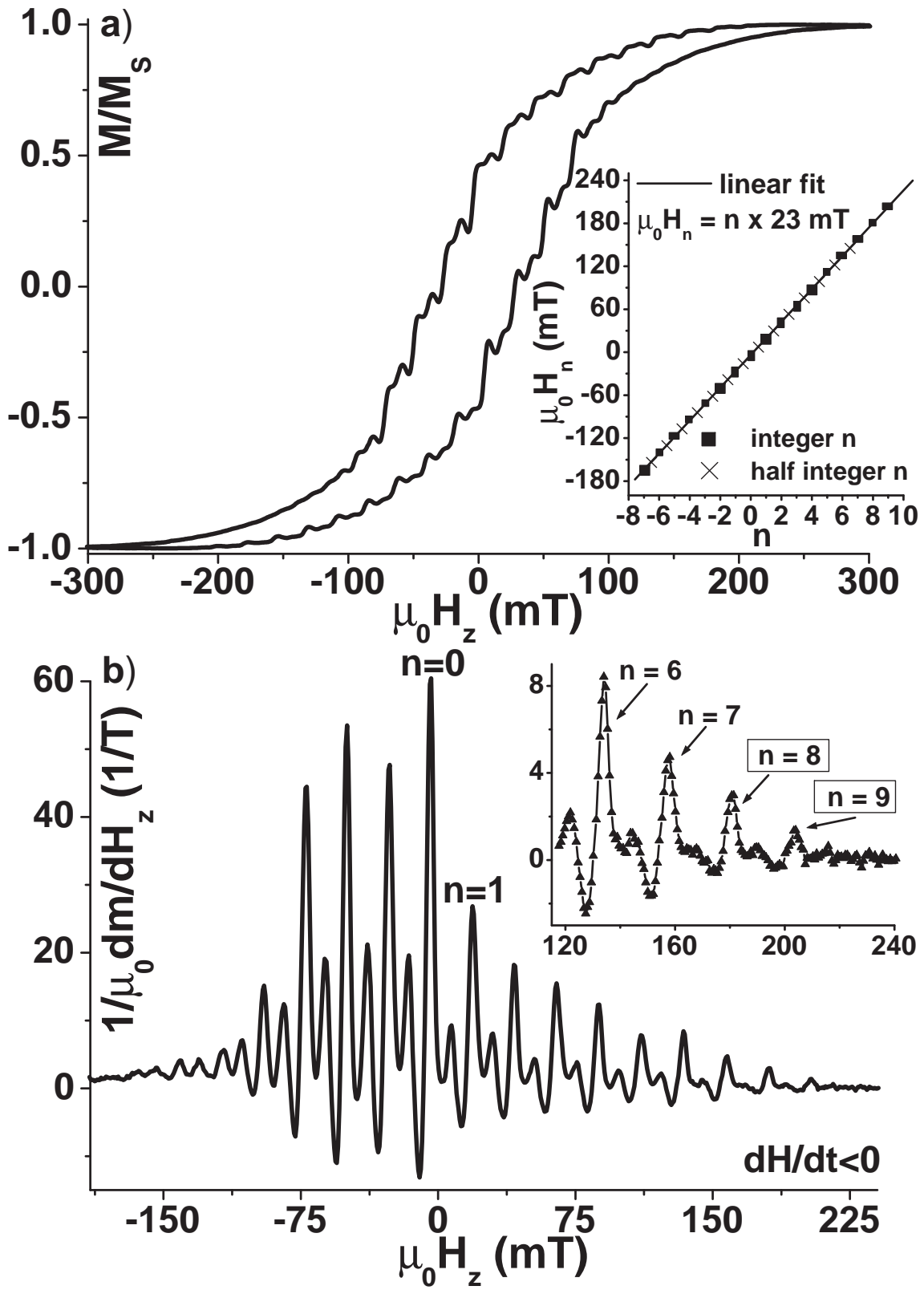


FIG. 3. R. Giraud

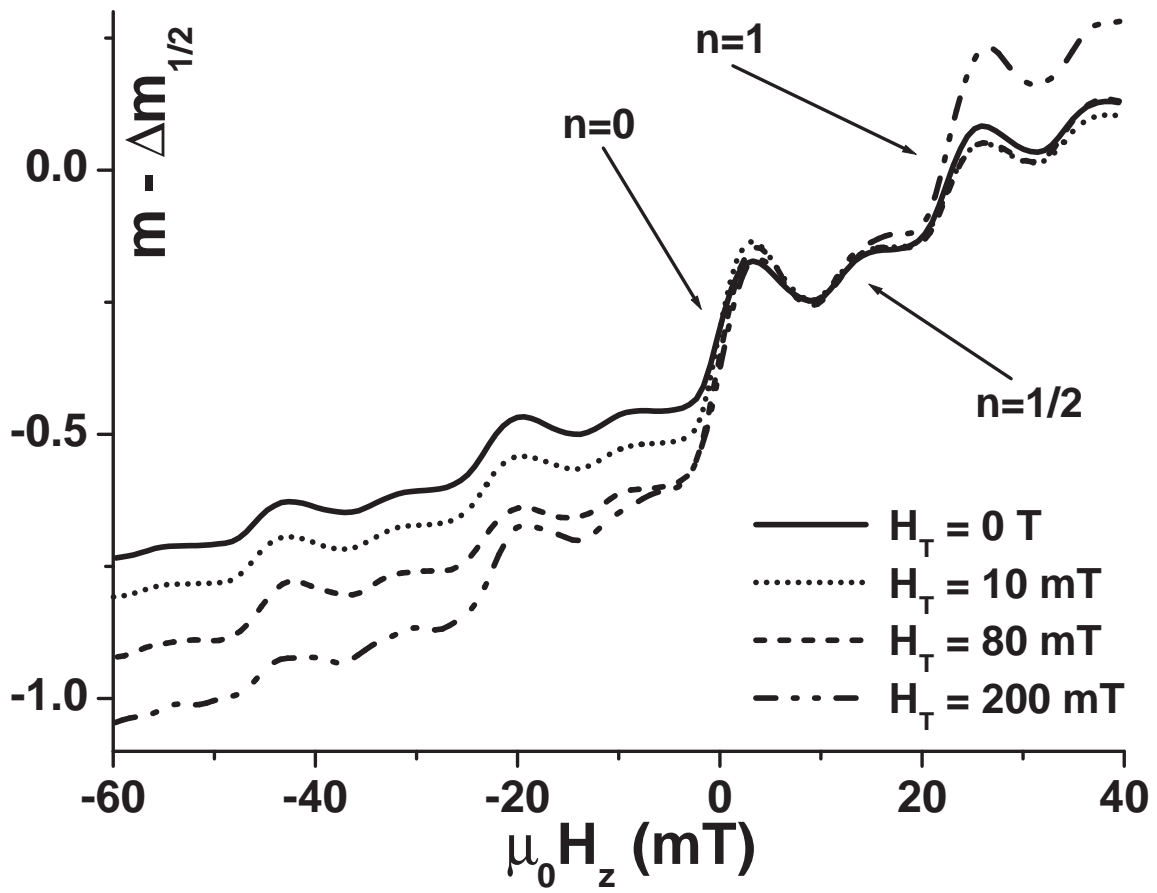


FIG. 4. R. Giraud